

Section I. (Amendment to the Claims)

A listing of claims 1-32 of the present application, which are amended herein with markings to show changes made, is provided below:

1-21. (Canceled).

22. (Currently amended) An electrical contact to a region of a silicon-containing substrate comprising:

a substrate having an exposed region of a silicon-containing semiconductor material, said silicon-containing semiconductor material being doped with an impurity to provide carriers of holes, electrons or both holes and electrons; and

a first layer of CoXSi_2 , wherein X is an alloying additive selected from the group consisting of C, Al, Sc, Ti, V, Cr, Mn, Fe, Cu, Ge, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, Ir, Pt, Ce, Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu and mixtures thereof, said alloying additive being present in said first layer in an amount of from about 0.01 to about 50 atomic %,

said first layer and said silicon-containing semiconductor material forming an interface having a predetermined roughness and being substantially free of Co silicide spikes descending into said silicon-containing semiconductor material.

23. (Cancelled).

24. (Currently amended) The electrical contact of Claim 22 ~~23~~ wherein said alloying additive is C, Al, ~~Si~~, Sc, Ti, V, Cr, Mn, Fe, ~~Co, Ni~~, Cu, Ge, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, Ir or Pt.

25. (Currently amended) The electrical contact of Claim 22 ~~24~~ wherein said alloying additive is ~~Si~~, Ti, V, Cr, ~~Cl~~, ~~Ni~~, Ge, Nb, Rh, Ta, Re or Ir.

26. (Original) The electrical contact of Claim 22 wherein said alloying additive is present in said first layer in an amount of from about 0.1 to about 20 atomic %.
27. (Currently amended) An electrical contact to a region of a silicon-containing substrate comprising:
a substrate having an exposed region of a silicon-containing semiconductor material, said silicon-containing semiconductor material being doped with an impurity to provide carriers of holes, electrons or both holes and electrons; and
a first layer of NiXSi, wherein X is an alloying additive selected from the group consisting of C, Al, Sc, Ti, V, Cr, Mn, Fe, Cu, Ge, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, Ir, Pt, Ce, Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu and mixtures thereof, said alloying additive being present in said first layer in an amount of from about 0.01 to about 50 atomic %,
said first layer and said silicon-containing semiconductor material forming an interface having a predetermined roughness and being substantially free of Ni silicide spikes descending into said silicon-containing semiconductor material.
28. (Canceled).
29. (Currently amended) The electrical contact of Claim 28 wherein said alloying additive is C, Al, ~~Si~~, Sc, Ti, V, Cr, Mn, Fe, ~~Ce, Ni~~, Cu, Ge, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, Ir or Pt.
30. (Currently amended) The electrical contact of Claim 29 wherein said alloying additive is ~~Si~~, Ti, V, Cr, ~~Ni~~, Ge, Nb, Rh, Ta, Re or Ir.
31. (Original) The electrical contact of Claim 27 wherein said alloying additive is present in said first layer in an amount of from about 0.1 to about 20 atomic %.
32. (Canceled).